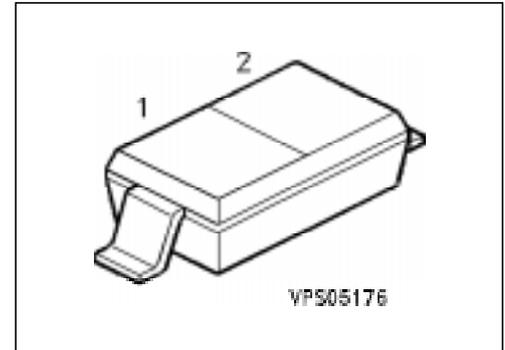


## Silicon RF Switching Diode

**BA 582**

- For low-loss VHF band switching in TV/VTR tuners



| Type   | Marking | Ordering Code | Pin Configuration | Package <sup>1)</sup> |
|--------|---------|---------------|-------------------|-----------------------|
| BA 582 | blue S  | Q62702-A829   |                   | SOD-123               |

### Maximum Ratings

| Parameter                                    | Symbol    | Values         | Unit |
|--|-----------|----------------|------|
| Reverse voltage                              | $V_R$     | 35             | V    |
| Forward current, $T_A \leq 60^\circ\text{C}$ | $I_F$     | 100            | mA   |
| Operation temperature range                  | $T_{op}$  | - 55 ... + 125 | °C   |
| Storage temperature range                    | $T_{stg}$ | - 55 ... + 150 |      |

### Thermal Resistance

|                    |             |            |     |
|--------------------|-------------|------------|-----|
| Junction - ambient | $R_{th,JA}$ | $\leq 600$ | K/W |
|--------------------|-------------|------------|-----|

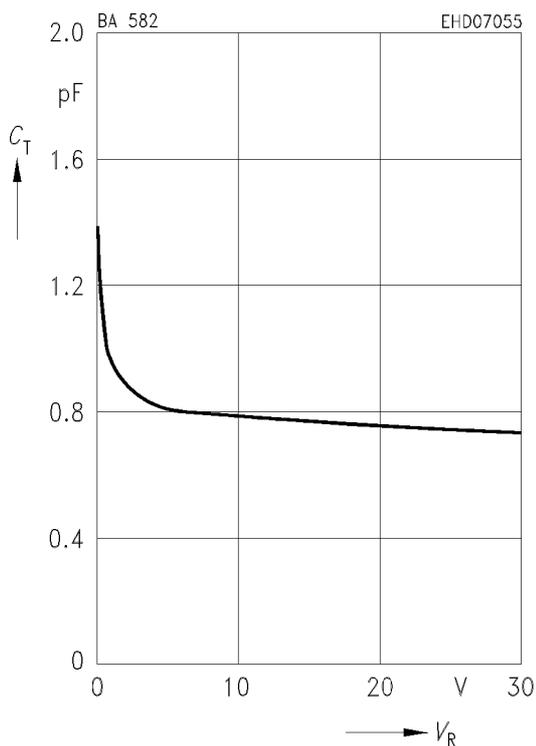
<sup>1)</sup> For detailed information see chapter Package Outlines.

## Electrical Characteristics

at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

| Parameter   | Symbol  | Values   |              |            | Unit       |
|---|---------|----------|--------------|------------|------------|
|   |         | min.     | typ.         | max.       |            |
| Forward voltage<br>$I_F = 100\text{ mA}$  | $V_F$   | –        | –            | 1          | V          |
| Reverse current<br>$V_R = 20\text{ V}$  | $I_R$   | –        | –            | 20         | nA         |
| Diode capacitance<br>$f = 1\text{ MHz}$<br>$V_R = 1\text{ V}$<br>$V_R = 3\text{ V}$       | $C_T$   | –<br>0.6 | 0.92<br>0.85 | 1.4<br>1.1 | pF         |
| Forward resistance<br>$f = 100\text{ MHz}$<br>$I_F = 3\text{ mA}$<br>$I_F = 10\text{ mA}$ | $r_f$   | –<br>–   | 0.45<br>0.38 | 0.7<br>0.5 | $\Omega$   |
| Reverse resistance<br>$V_R = 1\text{ V}, f = 100\text{ MHz}$                              | $1/g_p$ | –        | 100          | –          | k $\Omega$ |
| Series inductance   | $L_s$   | –        | 2.8          | –          | nH         |

**Diode capacitance  $C_T = f(V_R)$**   
 $f = 1\text{ MHz}$



**Forward resistance  $r_f = f(I_F)$**   
 $f = 100\text{ MHz}$

